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45W TYPE-C PD3.0 / QC3.0 Power Adapter Solution with WT6632F

ON	ON's Device App		lication	Input Volt	tage	Outpu	t Power	Topology	I/O Isolation
N NT	NCP4306D and N NTMFS6B03 suppo		ohone, PAD B adapter rting PD3.0 I QC3.0	90 Vac to 26	264 Vac 45 W		5 W	Flyback	lsolated (3 kV)
			PD C	Dutput Speci	ficatio	n	QC	Output Specifica	ation
	Output V	/oltage	5 V, 9 V, 12 V, 15 V, 20 V						
	Nominal	Current	5V/3A, 9V/3A, 12V/3A,15V3A, 20V/2.25A			5 V /	//3A		
	Max Current		5V/3A, 9V/3A, 12V/3A,15V3A, 20V/2.25A			V/2.25A	5 V / 3 A, 9 V / 3 A, 12 V / 3 A		
	Min Current		zero				zero		
	Ave		J. Efficiency	/ >90%	>90% @ 20 V 2.25 A at board end, 115 & 230 Vac				
			Ripple	pple			<100mV		
	Sta		ndby Power	ver <30mW @ 5 V			& 230 Vac (N		
	Po		wer Density	er Density			1.15W/cm^3		
	F		rotection	tion Adaptive UV		P, OVP, OVI			
	Size				57mmx36mmx19mm				

Circuit Description

This design note describes a 45 W, Type C interface PD2.0, universal AC input, constant voltage power supply intended for smart phone, PAD and NB adaptor supporting PD3.0 or QC3.0 protocol, where isolation from the AC mains is required, and low cost, high efficiency, and low standby power are essential.

The featured power supply is a simple QR flyback topology utilizing ON Semiconductor's NCP1340B3 HF PWM controller, NCP4306D synchronous rectified controller, NTMFS6B03 synchronous MOSFET and ATP104 Switch MOSFET. This Design Note provides the complete circuit schematic details, PCB and BOM for 45 W Type C Interface PD3.0 Power adapter solution which supports PD output (5 V / 3 A, 9 V / 3 A, 12 V / 3 A, 15 V / 3 A, 20 V / 2.25 A).

This design combined with Weltrend WT6632F PD3.0 protocol controller to provide PD3.0 and

QC3.0 functions. This design also proposes a dual auxiliary power supply to supply PWM controller, the PWM controller is supplied by high voltage auxiliary voltage at low output voltage and supplied by low voltage auxiliary voltage at high output voltage and also shuts down the Zener bias of high voltage Vcc while low voltage auxiliary voltage supplies controller.

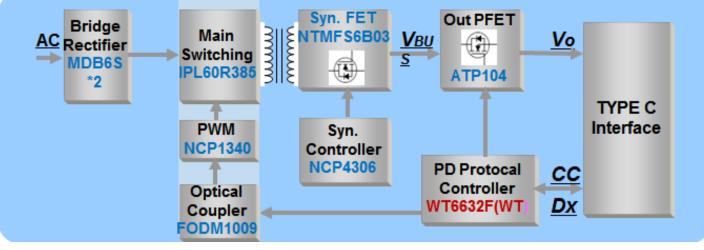
This design also uses NCP4306 synchronous rectified controller to provide high efficiency and also has no external Vcc regulator to supply synchronous controller to ensure controller can works below 3.6 V.

Key Features

- Universal AC input range (90 264 Vac)
- Very low standby (5 V & 230 Vac) power consumption with no cable plug in
- Very low ripple and noise
- Inherent SCP and OCP protection
- High operation frequency up to 150kHz

Block Diagram and Board Images

- High power density (1.15 W/cm³)
- Quick switching off FET while unplugging cable and switching on FET at Vbus dropping to 5 V while plugging cable again
- Quasi-Resonant current mode control with Valley Switching
- Valley lockout avoids audible noise at valley jumping operation
- Support TYPE-C PD3.0 & QC3.0 protocol
- Adaptive Output OVP and UVP
- Open loop protection
- Board size: 57mmx36mmx19mm



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Figure 1, High level schematic of 45 W TYPE-C PD adapter

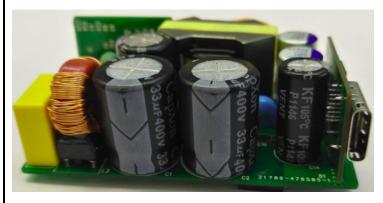
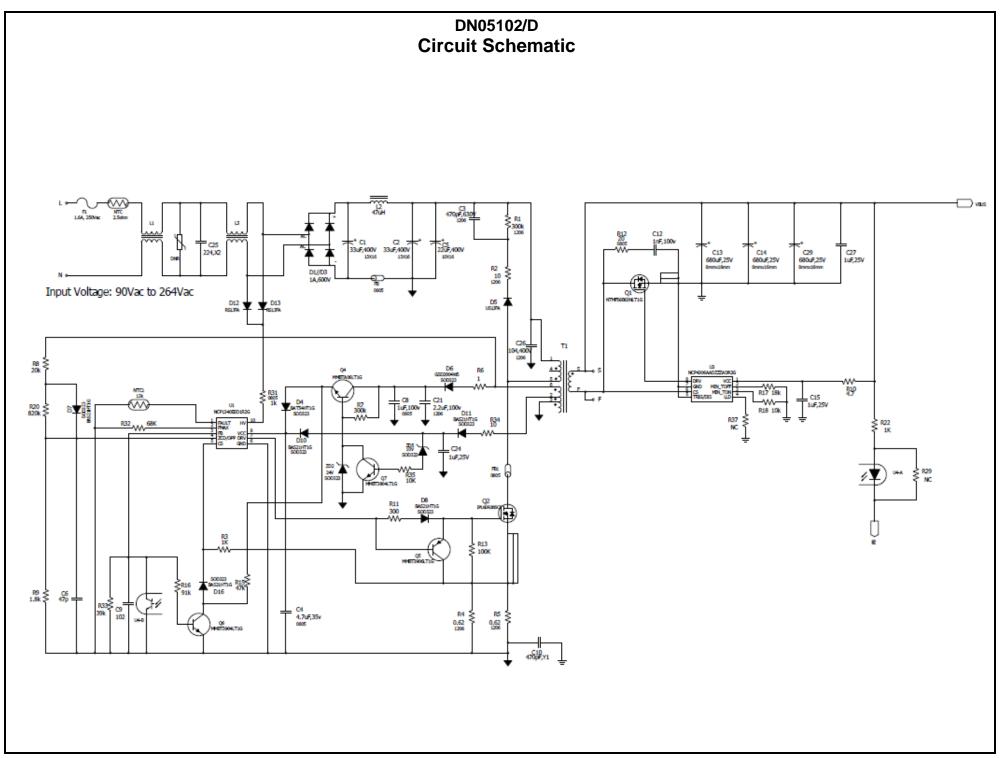
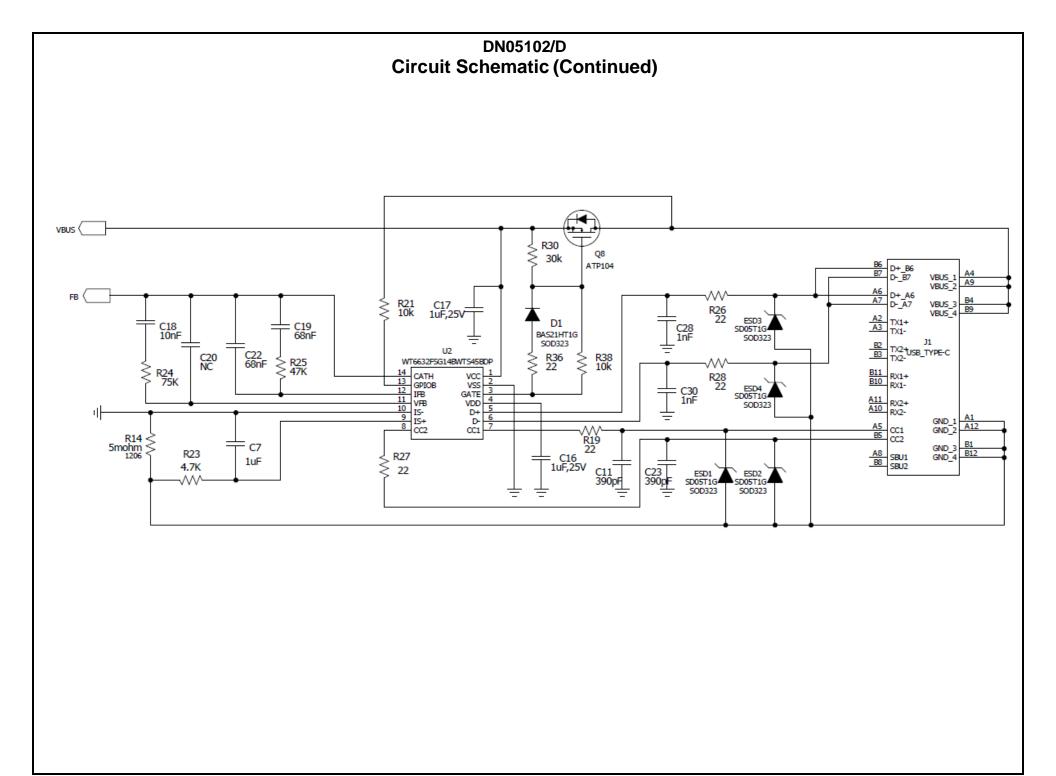


Figure 2, Side view 1 of the demo board



Figure 3, Side view 2 of the demo board





DN05102/D PCB

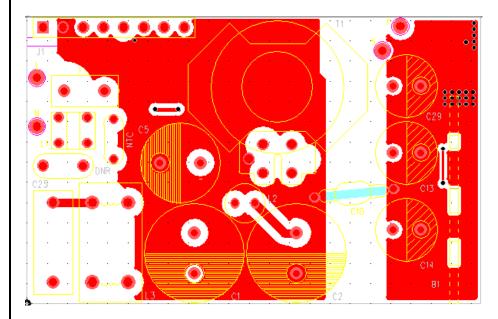


Figure 3, Top View of Mainboard's PCB

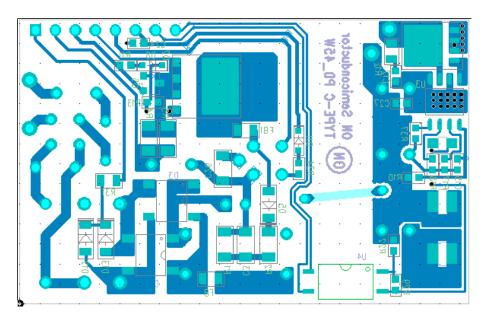


Figure 4, Bottom View of Mainboard's PCB

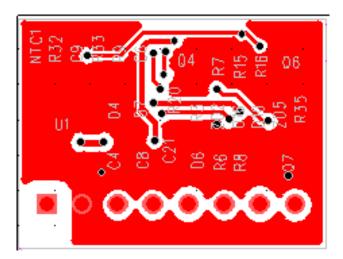


Figure 5, Top View of PWM control board's PCB

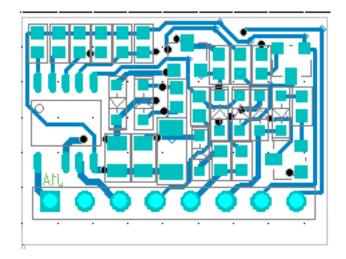


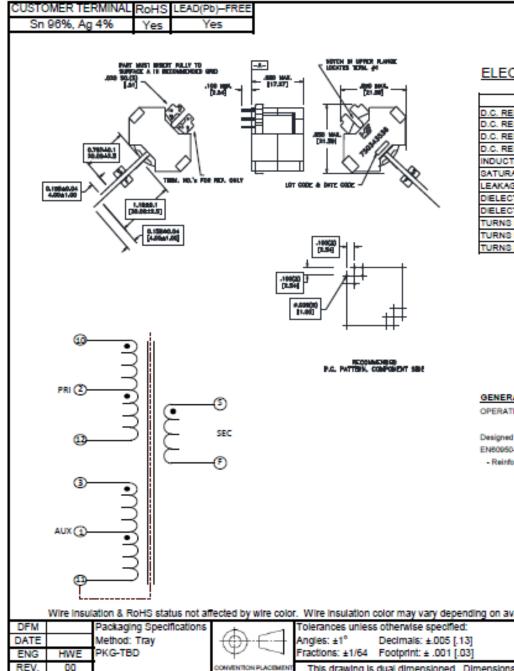
Figure 6, Bottom View of PWM control board's PCB

<section-header>

Figure 7, Top View of PD control board (WT6632F)'s PCB

Figure 8, Bottom View of PD control board (WT6632F)'s PCB

T1 Transformer Designs (Available from Wurth Electronics)



more than you expect



ELECTRICAL SPECIFICATIONS @ 25° C unless otherwise noted:

PARAMETER		TEST CONDITIONS	VALUE
D.C. RESISTANCE	10-12	@20°C	0.560 ohms max.
D.C. RESISTANCE	3-1	@20°C	0.380 ohms max.
D.C. RESISTANCE	1-11	@20°C	0.210 ohms max.
D.C. RESISTANCE	8-F	@20°C	0.021 ohms max.
INDUCTANCE	10-12	10kHz, 1V, Ls	360.00µH ±10%
SATURATION CURRENT	10-12	20% rolloff from initial	2.5A
LEAKAGE INDUCTANCE	10-12	tle(1+3+10+S+F),100kHz, 1V, Ls	5.5µH max.
DIELECTRIC	1-8	5e(1+2+3+10+11+12), 3750VAC, 1 second	3000VAC, 1 minute
DIELECTRIC	S-CORE	3750VAC, 1 second	3000VAC, 1 minute
TURNS RATIO		(10-12):(3-1)	3.25:1, ±2%
TURNS RATIO		(10-12):(1-11)	6.5:1, ±2%
TURNS RATIO		(10-12):(S-F)	6.5:1, ±2%

GENERAL SPECIFICATIONS:

OPERATING TEMPERATURE RANGE: -40°C to +125°C including temp rise.

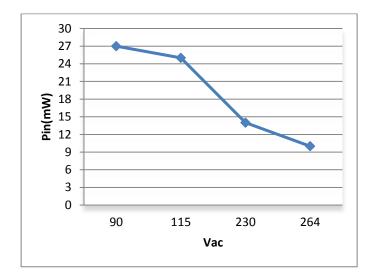
Designed to comply with the following requirements as defined by IEC60950-1, EN60950-1, UL60950-1/CSA60950-1 and ASINZS60950.1:

Reinforced insulation for a primary circuit at a working voltage of 285Vrms, 400Vpeak, Overvoltage Category II.

L	Wire insulation & RoHS status not affected by wire color. Wire insulation color may vary depending on availability.									
	FΜ		Packaging Specifications	1	Tolerances unless otherwise specified:	DRAWING TITLE	PART NO.			
D	ATE		Method: Tray	(()) .E	Angles: ±1° Decimals: ±.005 [.13]	TRANSFORMER				
E	NG	HWE	PKG-TBD	$\Psi \sim$	Fractions: ±1/64 Footprint: ± .001 [.03]	TRANSFORMER	750343635			
R	EV.	00		CONVENTION PLACEMENT	This drawing is dual dimensioned. Dimensions in	1	750545055			
D	ATE	6/30/2017	www.www.unites.com/minutes		brackets are in millimeters.		SPECIFICATION SHEET 1 OF 1			
_										

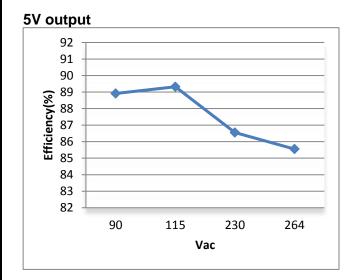
DN05102/D

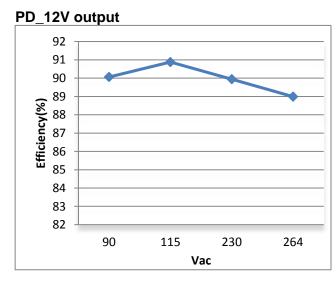
DN05102/D Standby Power at 5V Output (Cable unplug) @ 90 Vac to 264 Vac Input Test condition: all efficiency are tested at board end



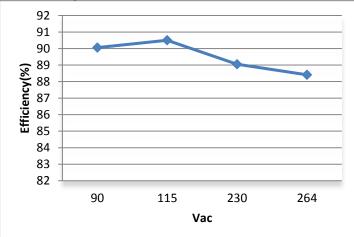
Average Efficiency

Test condition: all efficiency are tested at board end

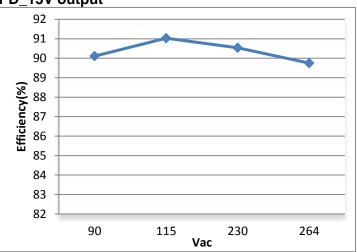






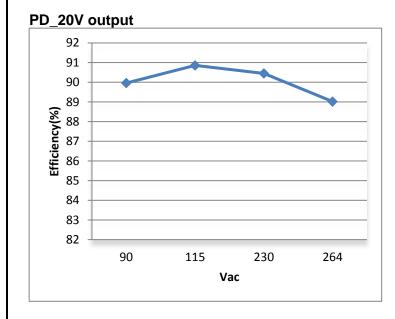






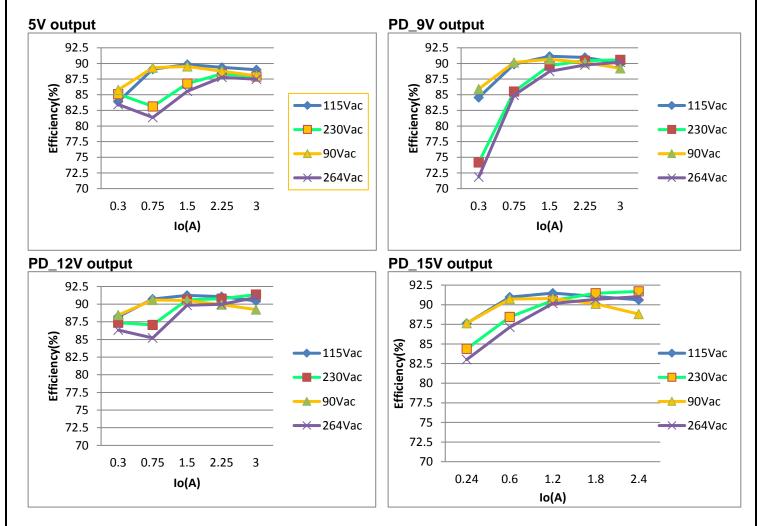
Average Efficiency (Continued)

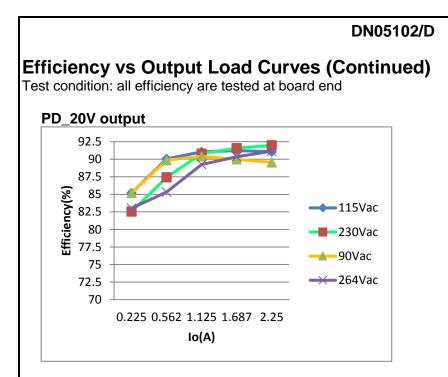
Test condition: all efficiency are tested at board end



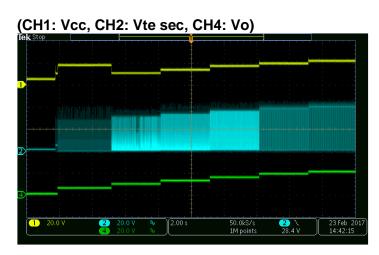
Efficiency vs Output Load Curves

Test condition: all efficiency are tested at board end

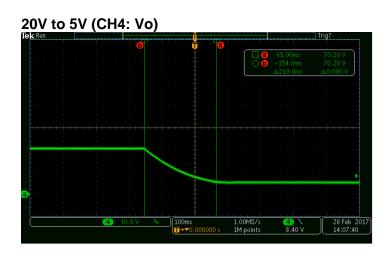




Power On and PD Voltage Change (5V > 9V > 12V > 15V > 18V >20V)

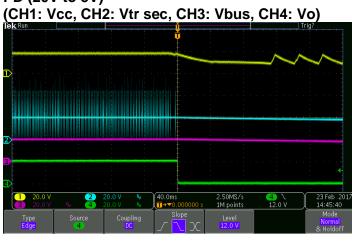


PD Transition with PD Emulator

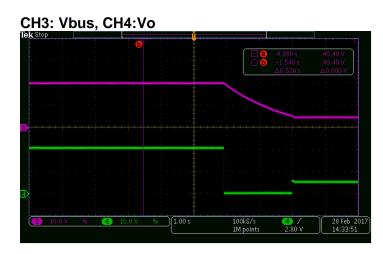


Discharge Time @ Cable Unplug

PD (20V to 5V)

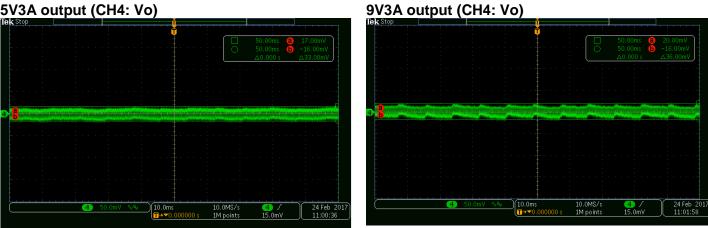


Quick Unplug/Plug Cable



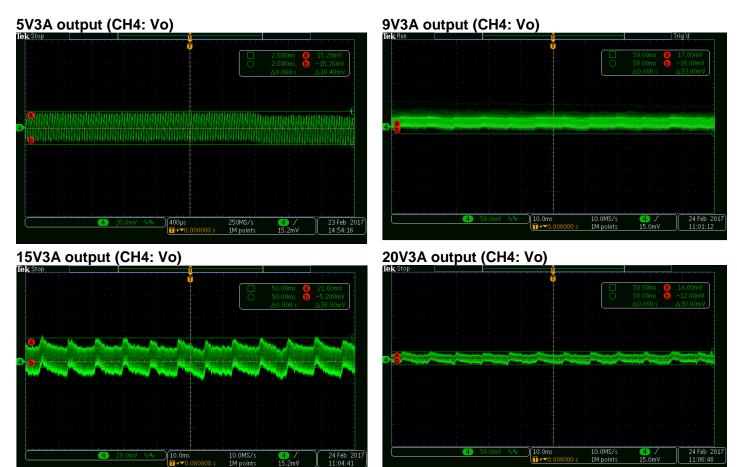
Output Ripple @ 90 Vac Input, 3A Output

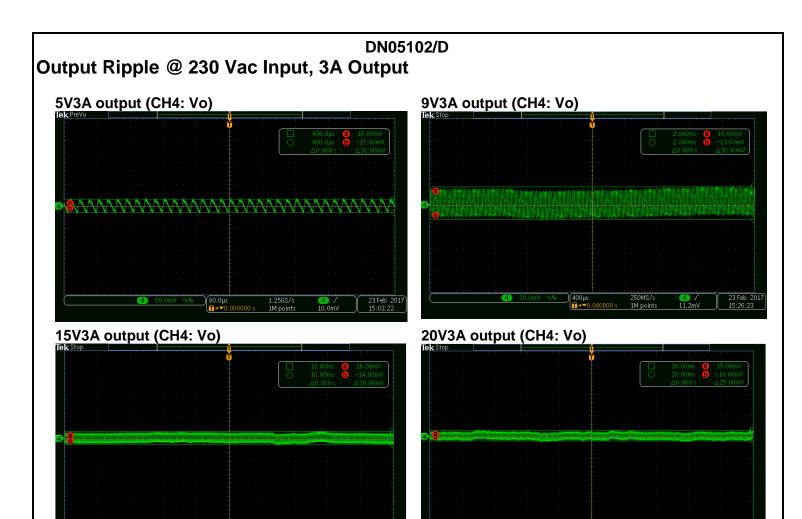
5V3A output (CH4: Vo)



DN05102/D Output Ripple @ 90 Vac Input, 3A Output (Continued)

Output Ripple @ 115 Vac Input, 3A Output



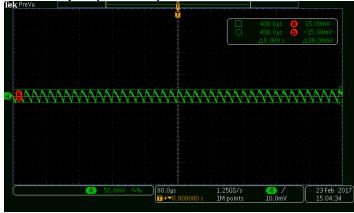


Output Ripple @ 264 Vac Input, 3A Output

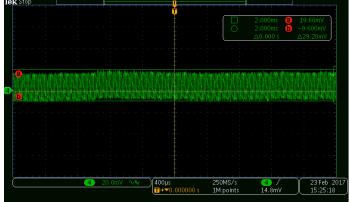
2.00m:

50.0MS/s 1M points کر 🚯 ۷۳00.9 23 Feb 20 15:35:45





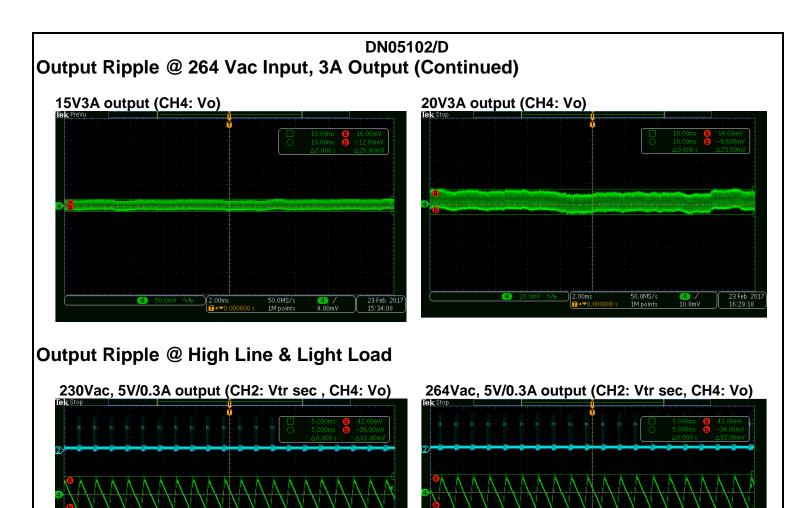
9V3A output (CH4: Vo)



4.00ms

25.0MS/s 1M points

4 11.0r 23 Feb 201 16:28:35



23 Feb 2

23 Feb 2 17:39:26

100MS/s 1M point:

100MS/s 1M points

4 16.0m√

<mark>4</mark> 16 On

1.00ms

1.00ms

264Vac, 15V/0.15A output (CH2: Vtr sec, CH4: Vo)

1.00ms □→▼0.000000 s

264Vac, 20V/0.1A output (CH2: Vtr sec, CH4: Vo)

1.00m: **1**→▼0

2

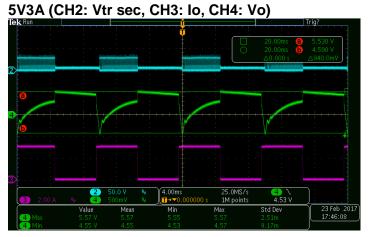
100MS/s 1M points

100MS/s 1M point 4 16.0n

(4) \. 16.0mV 23 Feb 20 17:35:37

23 Feb 20 17:40:00

Dynamic Test @ 115 Vac Input



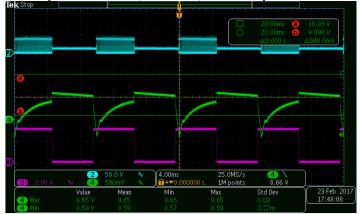
Test condition: 0-3A, 10mS cycle, 125mA/Us 1m cable, tested at E-load 12V3A (CH2: Vtr sec, CH3: Io, CH4: Vo)



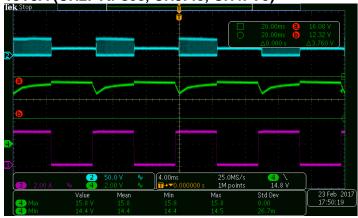
Test condition: 0-3A, 10mS cycle, 125mA/Us 1m cable, tested at E-load 20V2.25A (CH2: Vtr sec, CH3: Io, CH4: Vo)



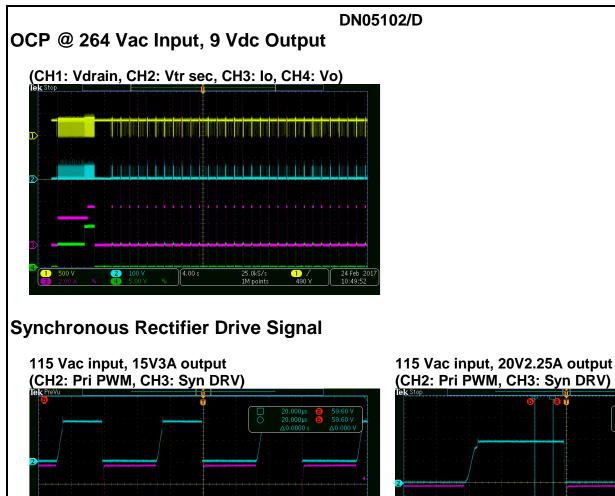
Test condition: 0-2.25A, 10mS cycle, 125mA/Us 1m cable, tested at E-load 9V3A (CH2: Vtr sec, CH3: Io, CH4: Vo)

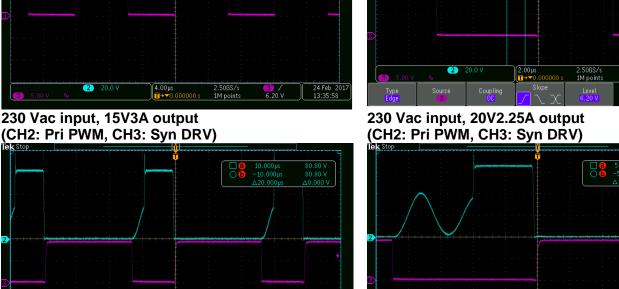


Test condition: 0-3A, 10mS cycle, 125mA/Us 1m cable, tested at E-load 15V3A (CH2: Vtr sec, CH3: Io, CH4: Vo)



Test condition: 0-3A, 10mS cycle, 125mA/Us 1m cable, tested at E-load





Туре

2

2 20.0

230 Vac input, 15V3A output

2

20.0 V

2.00µs

4.00μs Π→▼0.000000 s

2.50GS/s 1M points

<mark>3</mark> ∫ 6.20 V

24 Feb 201 13:38:58

24 Feb 2 13:41:09

80.80 V

24 Feb 201 13:39:50

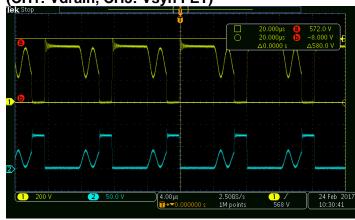
<mark>3</mark> ∕ 6.20 V

2.50GS/s 1M points

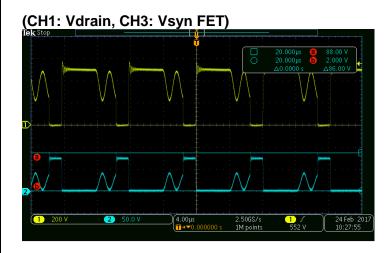
3 / 6.20 V

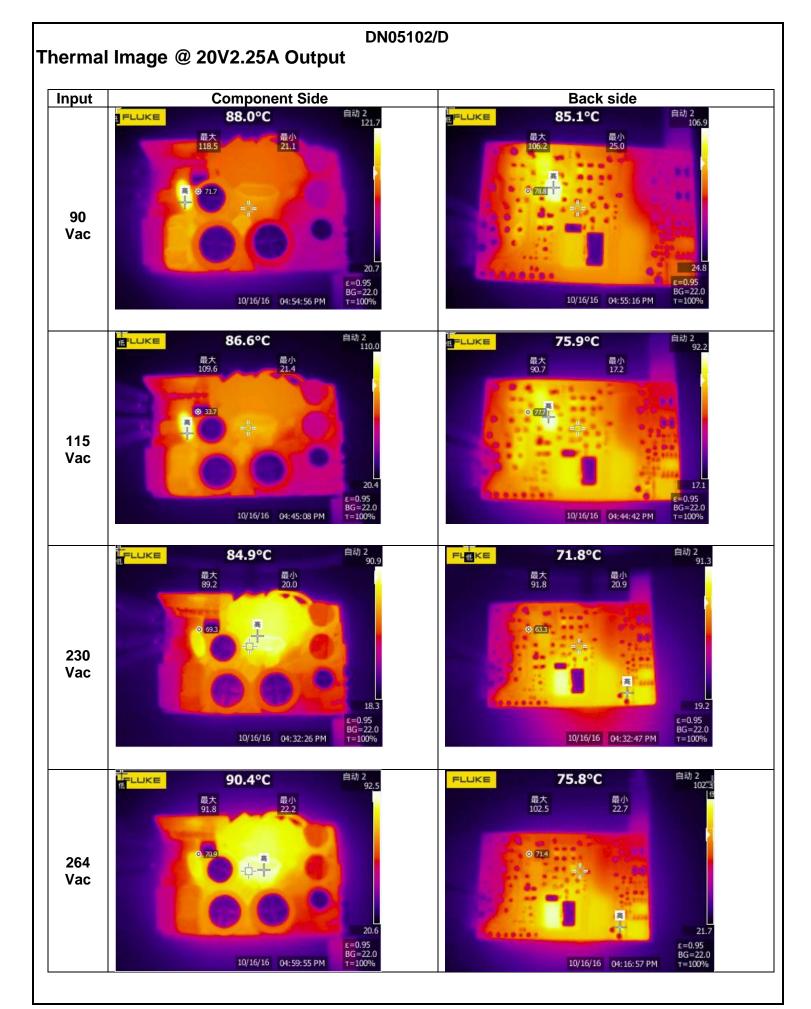
1.00µs





Synchronous FET Drain Voltage @ 264 Vax input, 20V2.25A output





	DN05102/D BOM									
Item	Qty	Reference	Туре	Part Name	MFR	Value	Package	Description		
1	1	C9	Ceramic Capacitor	Std	std	102	603	Capacitor, Ceramic, 50V, 10%		
2	1	C26	Ceramic Capcitor		TDK	104, 400V	1206	Capacitor, Ceramic, SMD, 5%		
3	1	C18	Ceramic Capacitor	Std	std	10nF	603	Capacitor, Ceramic, 50V, 10%		
4	2	C28 C30	Ceramic Capacitor	std	std	1nF	603	Capacitor, Ceramic, 50V, 10%		
5	1	C12	Ceramic Capacitor	C1608C0G2A102J	TDK	1nF, 100v	603	Capacitor, Ceramic, SMD, 5%		
6	5	C15-17 C24 C2	Ceramic Capacitor	C1608X7R1E105K	TDK	1uF, 25V	603	Capacitor, Ceramic, 25V, 10%		
7	1	C8	Ceramic Capacitor	C3216X7S2A225K	TDK	2. 2uF, 100v	1206	Capacitor, Ceramic, 100V, 10%		
8	1	C21	Ceramic Capacitor	C2012X7S2A105K	TDK	1uF, 100v	805	Capacitor, Ceramic, 100V, 10%		
9	1	C25	X2 Capcitor	/890334022017	Wueth	224, X2	THT, 7.5	X2 capacitor, Safety standard approved, 10		
10	2	C11 C23	Ceramic Capacitor	std	std	390pF	603	Capacitor, Ceramic, 50V, 10%		
11	1	C4	Ceramic Capacitor	C2012X7R1V475K	TDK	4. 7uF, 35v	805	Capacitor, Ceramic, 35V, 10%		
12	1	C3	Ceramic Capcitor	C3216C0G2J471J	TDK	470pF, 630V	1206	Capacitor, Ceramic, Chip, 5%		
13	1	C10	Ceramic Capcitor	CS65-B2GA101KYNI	TDK	470pF, Y1	Lead typ	HV Ceramic Capacitor, safety standard appro		
14	1	C6	Ceramic Capacitor	Std	std	47p	603	Capacitor, Ceramic, 50V, 10%		
15	1	C7	Ceramic Capacitor	Std	std	1uF, 25v	603	Capacitor, Ceramic, 25V, 10%		
16	2	C19 C22	Ceramic Capacitor	Std	std	68nF	603	Capacitor, Ceramic, 50V, 10%		
17	1	C20	Ceramic Capacitor	Std	std	NC	603	Capacitor, Ceramic, 50V, 10%		
18	1	D1 D3	Bridge rectifier	MDB6S	ON(FSC)	1A, 600V	Micro-D	Bridge Rectifier, 600V, 1A		
19	1	DNR	Varistor	820573011	Wurth	10D471K	TH	Varistor, 10D471K		
20	5	D1 D7 D10-11	Switching diode	BAS21HT1G	ON	0.2A,250V	S0D323	Switching diode, SMD		
21	1	D6	Switching diode	GSD2004WS	Vishay	0.2A, 300V	S0D323	Switching diode, SMD		
22	1	D4	Switching diode	BAT54HT1G	ON	0.2A,30V	S0D323	Switching diode, SMD		
23	1	D5	Ultrafast rectifi	US1JFA	ON(FSC)	0.8A,600V	SOD123FI	Standard Rectifier, 0.8A, 600V		
24	2	D12-13	Standard rectifie	RS1JFA	ON(FSC)	0.8A,600V	SOD123FI	Standard Rectifier, 0.8A, 600V		
25	1	D8	Switching diode	BAS21HT1G	ON	0.2A,250V	S0D323	Switching diode, SMD		
26	1	FB	Ferrite bead	UPZ2012E102-1R57	Sunlord	/Wueth	805	1000ohm@100MHz		
27	1	FB1	Ferrite bead	UPZ2012E601-2R07	Sunlord	/Wueth	805	600ohm@100MHz		
28	1	L3	Common filter	744821110	Wueth	10mH	TH type	CM Filter, T type core		
29	1	L1	Common filter	150-1327	Wurth-M	500uH	TH	T type, 6.3x3x3, 11T, 0.2mmx2 in parallel winding		
30	1	F1	Fuse	20Т-016Н	Hollyfu	1.6A, 250V	Axial le	Micro Fuse, 1.6A/250V		
31		Q4	NPN Transistor	MMBTA06LT1G	ON	,	SOT23	General NPN Transistor, SMD		

DN05102/D BOM (Continued)

					(0011			
Item	Qty	Reference	Туре	Part Name	MFR	Value	Package	Description
32	2	Q6-7	NPN Transistor	MMBT3904LT1G	ON		SOT23	General NPN Transistor, SMD
33	1	Q5	PNP Transistor	MMBT3906LT1G	ON		SOT23	General PNP Transistor, SMD
34	1	U3	Syn. rectified co	NCP4306AADZZZADI	ON		S08	Syn. Rectified Controller
35	1	U1	PWM Controller	NCP1340B3D1R2G	ON		SOP9	QR PWM controller
36	1	NTC1	NTC	std	std	13k	603	replaced by 13k resisotor
37	1	NTC	NTC	SPNL09D2R5MBI	Sunlord	2.5ohm	lead typ	9mm Die, 2.5ohm
38	1	U4	Optical coupler	FODM1009	ON (FSC)		LSOP4	optical coupler, standard SOP package
39	1	Q8	PMOS	ATP104	ON	-30V, 8.4m	ATPAK	PMOS
40	1	L2	Axial leaded fixe	7447462470	Wurth	47uH		Axial leaded fixed inductor
41	1	Q2	MOSFET	IPL60R385CP	Infineo	n	THINKPAK	MOSFET, NChan, 600V
42	1	R6	Resistor	Std	Std	1	603	Resistor, Chip, 1/8W, 1%
43	1	R34	Resistor	Std	Std	10	603	Resistor, Chip, 1/8W, 1%
44	1	R13	Resistor	Std	Std	100K	603	Resistor, Chip, 1/8W, 1%
45	1	R35	Resistor	Std	Std	10K	603	Resistor, Chip, 1/8W, 1%
46	3	R18 R21 R38	Resistor	Std	Std	10k	603	Resistor, Chip, 1/8W, 1%
47	1	R17	Resistor	Std	Std	18k	603	Resistor, Chip, 1/8W, 1%
48	1	R3	Resistor	Std	Std	1K	603	Resistor, Chip, 1/8W, 1%
49	1	R22	Resistor	Std	Std	1K	603	Resistor, Chip, 1/8W, 1%,
50	1	R8	Resistor	Std	Std	20k	603	Resistor, Chip, 1/8W, 1%
51	5	R19 R26-28 R	Resistor	Std	Std	22	603	Resistor, Chip, 1/8W, 1%
52	1	R9	Resistor	Std	Std	1.8k	603	Resistor, Chip, 1/8W, 1%
53	1	R11	Resistor	Std	Std	300	603	Resistor, Chip, 1/8W, 1%
54	1	R7	Resistor	Std	Std	300k	603	Resistor, Chip, 1/8W, 1%
55	1	R30	Resistor	Std	Std	30k	603	Resistor, Chip, 1/8W, 1%
56	1	R33	Resistor	Std	Std	39k	603	Resistor, Chip, 1/8W, 1%
57	1	R10	Resistor	Std	Std	4.7	603	Resistor, Chip, 1/8W, 1%
58	1	R23	Resistor	Std	Std	4.7K	603	Resistor, Chip, 1/8W, 1%
59	1	R25	Resistor	Std	Std	47K	603	Resistor, Chip, 1/8W, 1%
60	1	R15	Resistor	Std	Std	47k	603	Resistor, Chip, 1/8W, 1%
61	1	R32	Resistor	Std	Std	68K	603	Resistor, Chip, 1/8W, 1%
62	1	R24	Resistor	Std	Std	75K	603	Resistor, Chip, 1/8W, 1%
63	1	R20	Resistor	Std	Std	820k	603	Resistor, Chip, 1/8W, 1%

	DN05102/D BOM (Continued)									
Item	Qty	Reference	Туре	Part Name	MFR	Value	Package	Description		
64	1	R16	Resistor	Std	Std	91k	603	Resistor, Chip, 1/8W, 1%		
65	1	R29	Resistor	Std	Std	NC	603	Resistor, Chip, 1/8W, 1%,		
66	1	R37	Resistor	Std	Std	NC	603	Resistor, Chip, 1/8W, 1%		
67	2	R4-5	Resistor	ERJ8BQFR062V	Panason	0.62	1206	Resistor, Chip, 1/2W, 1%		
68	1	R2	Resistor	Std	Std	10	1206	Resistor, Chip, 1/4W, 1%		
69	1	R31	Resistor	Std	Std	1k	805	Resistor, Chip, 1/5W, 1%		
70	1	R12	Resistor	Std	Std	20	805	Resistor, Chip, 1/5W, 1%		
71	1	R1	Resistor	Std	Std	300k	1206	Resistor, Chip, 1/4W, 1%		
72	1	R14	Resistor	ERJ8BWFR005V	Panason	5mohm	1206	Resistor, Chip, 1/2W, 1%		
73	1	T1	Transformer	750343635	WE-midc	on	TH type	RM8, 12Pin		
74	1	C5	Electrolytic capa	KM series/ERK2G	CapXon/	22uF, 400V	10X16	size,13mmx16mm		
75	2	C1-2	Electrolytic capa	KM series	CapXon	33uF, 400V	13X16	size,10mmx16mm		
76	3	C13-14 C29	Electrolytic soli	PS681M025F080P	CapXon	680uF, 25V	8mmx16mm	rsize:8mmx16mm		
77	1	Q1	MOSFET	NTMFS6B03NLT1G	ON		S08FL	MOSFET, NChan, 100V		
78	1	J1	USB Type C connec	632 723 300 011	Wueth		TH/SMD	Type C connector, SMT		
79	1	U2	PD controller	WT6632FSG14BWTS4	Weltren	d	S014	PD3.0/QC3.0 protocal controller		
80	1	ZD5	Zener	MM3Z10VT1G	ON	10V	S0D323	GENERIC ZENER-DIODE		
81	1	ZD2	Zener	MM3Z24VT1G	ON	24V	S0D323	GENERIC ZENER-DIODE		
82	4	ESD1-4	ESD	SD05T1G	ON	5V	S0D323	ESD protection device		
		1			1			1		

References

ON Semiconductor datasheet for NCP1340, 4306, NTMFS6B03, ATP104

ON Semiconductor Design Notes DN05043

Weltrend semiconductor datasheet for WT6632F

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